

Title (en)

A method for fabricating an interlayer-dielectric film of semiconductor device.

Title (de)

Verfahren zur Herstellung der dielektrischen Zwischenschicht einer Halbleitervorrichtung.

Title (fr)

Procédé de fabrication de la couche intermédiaire diélectrique d'un dispositif semi-conducteur.

Publication

EP 0540321 A1 19930505 (EN)

Application

EP 92309892 A 19921028

Priority

KR 910019176 A 19911030

Abstract (en)

The limit of B and P concentrations is surmounted by changing the surface of borophosphosilicate glass with a surface treatment such as plasma (3) processing of N<6>O, O<7> or O<6>, and encroachment caused by H<6>SO<8> boiling or by humidity absorption from the exterior is also removed such that low temperature reflow process below 850 DEG C is established and an interlayer dielectric film (2) of excellent planarity is formed. <IMAGE>

IPC 1-7

H01L 21/3105; **H01L 21/90**

IPC 8 full level

H01L 21/3105 (2006.01); **H01L 21/316** (2006.01); **H01L 21/768** (2006.01)

CPC (source: EP KR US)

H01L 21/02129 (2013.01 - US); **H01L 21/02271** (2013.01 - EP US); **H01L 21/0234** (2013.01 - EP US); **H01L 21/02343** (2013.01 - EP US); **H01L 21/283** (2013.01 - KR); **H01L 21/31** (2013.01 - KR); **H01L 21/3105** (2013.01 - EP US); **H01L 21/31625** (2013.01 - US); **H01L 21/76826** (2013.01 - EP US); **H01L 21/76834** (2013.01 - EP US); **H01L 21/02126** (2013.01 - EP); **H01L 21/02129** (2013.01 - EP); **H01L 21/02131** (2013.01 - EP); **H01L 21/02274** (2013.01 - EP)

Citation (search report)

- [A] US 4799992 A 19890124 - RAO KALIPATNAM V [US], et al
- [XP] DATABASE WPIL Section Ch, Week 4292, Derwent Publications Ltd., London, GB; Class L, AN 92-343076 & JP-A-4 245 630 (KAWASAKI STEEL CORP.) 2 September 1992
- [A] PATENT ABSTRACTS OF JAPAN vol. 012, no. 320 (E-651)30 August 1988 & JP-A-63 086 426 (TOSHIBA CORP.) 16 April 1988
- [A] PATENT ABSTRACTS OF JAPAN vol. 014, no. 455 (E-0985)28 September 1990 & JP-A-2 181 952 (SONY CORP.) 16 July 1990

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